

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

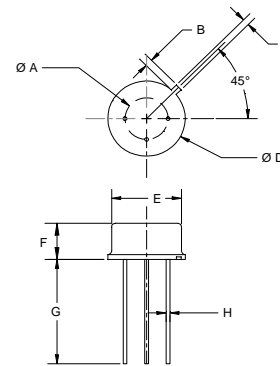
The **ASI ULBM2TE** is Designed for Class C, FM Land Mobile Applications up to 470 MHz.

**FEATURES:**

- Common Emitter
- $P_G = 8.0$  dB at 2.0 W/470 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	0.40 A
$V_{CBO}$	36 V
$V_{CEO}$	16 V
$V_{EBO}$	4.0 V
$P_{DISS}$	5 W @ $T_C = 25^\circ\text{C}$
$T_J$	-65 °C to +200°C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	35 °C/W

**PACKAGE STYLE TO-39GE**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.200 / 5.080	
B	.029 / 0.740	.045 / 1.140
C	.028 / 0.720	.034 / 0.860
D	.355 / 9.020	.370 / 9.370
E	.315 / 8.010	.335 / 8.500
F	.165 / 4.200	.180 / 4.570
G	.500 / 12.700	.750 / 19.050
H	.016 / 0.410	.020 / 0.508

**ORDER CODE: ASI10679**
**CHARACTERISTICS**  $T_C = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 50$ mA	16			V
$BV_{CES}$	$I_C = 50$ mA $R_{BE} = 10 \Omega$	36			V
$BV_{EBO}$	$I_E = 1.0$ mA	4.0			V
$I_{CBO}$	$V_{CB} = 15$ V			1.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 50$ mA	20		200	---
$C_{ob}$	$V_{CB} = 12.5$ V $f = 1.0$ MHz			10	pF
$P_G$ $\eta_c$	$V_{CE} = 12.5$ V $P_{OUT} = 2.0$ W $f = 470$ MHz	8.0	55		dB %